Abstracts

Improved parameter extraction of small-sized FETs for low-power applications

F. Lenk and R. Doerner. "Improved parameter extraction of small-sized FETs for low-power applications." 2000 MTT-S International Microwave Symposium Digest 00.3 (2000 Vol. III [MWSYM]): 1389-1392.

In low-power applications FETs with small gate width are required. For such devices common extraction methods fail. In particular, extracting source inductance and drain pad capacitance using "cold"-FET measurements is no longer possible. We present an improved method that allows reliable extraction of extrinsic elements for small-sized FETs.

❑ Return to main document.